



# PNP Silicon Planar Epitaxial Transistors

## FEATURES

Power dissipation

$$P_{CM}: 0.625 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

$$I_{CM}: -0.1 \text{ A}$$

Collector-base voltage

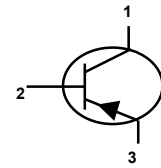
$V_{CBO}$ :	BC556	-80	V
	BC557	-50	V
	BC558	-30	V

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$



- 1. COLLECTOR
- 2. BASE
- 3. EMITTER



**TO-92**

## Electrical Characteristics (Ta=25 °C unless otherwise specified)

			SPEC	min	max	unit	
Collector-base breakdown voltage	BC556	$V_{CBO}$	$I_C = -100\mu\text{A}, I_E = 0$	-80		V	
	BC557			-50			
	BC558			-30			
Collector-emitter breakdown voltage	BC556	$V_{CEO}$	$I_C = -2\text{mA}, I_B = 0$	-65		V	
	BC557			-45			
	BC558			-30			
Emitter-base breakdown voltage		$V_{EBO}$	$I_E = -100\mu\text{A}, I_C = 0$	-6		V	
Collector cut-off current	BC556	$I_{CBO}$	$V_{CB} = -70\text{V}, I_E = 0$			$\mu\text{A}$	
	BC557			$V_{CB} = -45\text{V}, I_E = 0$			-0.1
	BC558			$V_{CB} = -25\text{V}, I_E = 0$			
Collector cut-off current	BC556	$I_{CEO}$	$V_{CE} = -60\text{V}, I_B = 0$			$\mu\text{A}$	
	BC557			$V_{CE} = -40\text{V}, I_B = 0$			-0.1
	BC558			$V_{CE} = -25\text{V}, I_B = 0$			
Emitter cut-off current	BC556	$I_{EBO}$	$V_{EB} = -5\text{V}, I_C = 0$			$\mu\text{A}$	
	BC557						-0.1
	BC558						
DC current gain	BC556	$h_{FE(1)}$	$V_{CE} = -5\text{V}, I_C = -2\text{mA}$	120	500		
	BC557			120	800		
	BC558			120	800		
	BC557A			120	220		
	BC556B/BC557B/BC558B			180	460		
	BC557C			420	800		
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = -100\text{mA}, I_B = -5\text{mA}$		-0.3	V	
Base-emitter saturation voltage		$V_{BE(sat)}$	$I_C = -100\text{mA}, I_B = -5\text{mA}$		-1	V	
Transition frequency		$f_T$	$V_{CE} = -5\text{V}, I_C = -10\text{mA}$ $f = 100\text{MHz}$	150		MHz	